Supporting Information

Interaction at the silicon/transition metal oxide heterojunction interface and its effect on the photovoltaic performance

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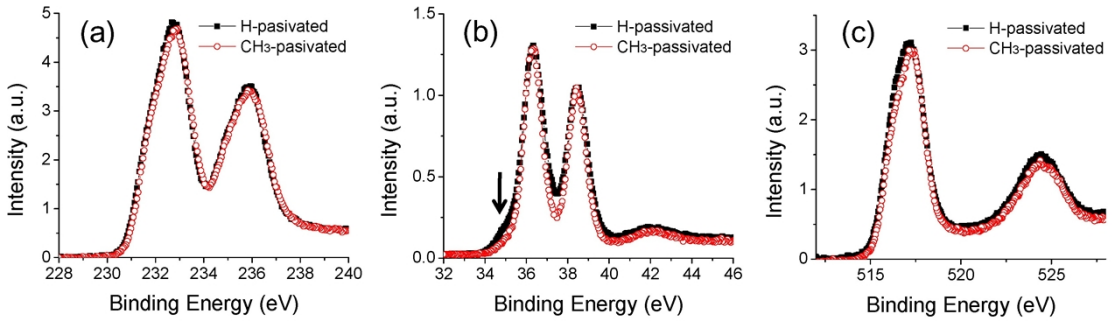

Figure S1 (a) The Mo 3d peak of the MoO_{3-x} thin film. (b)The W 4f peak of the WO_{3-x} thin film. (c) The V 2p peak of the V_2O_{5-x} thin film.

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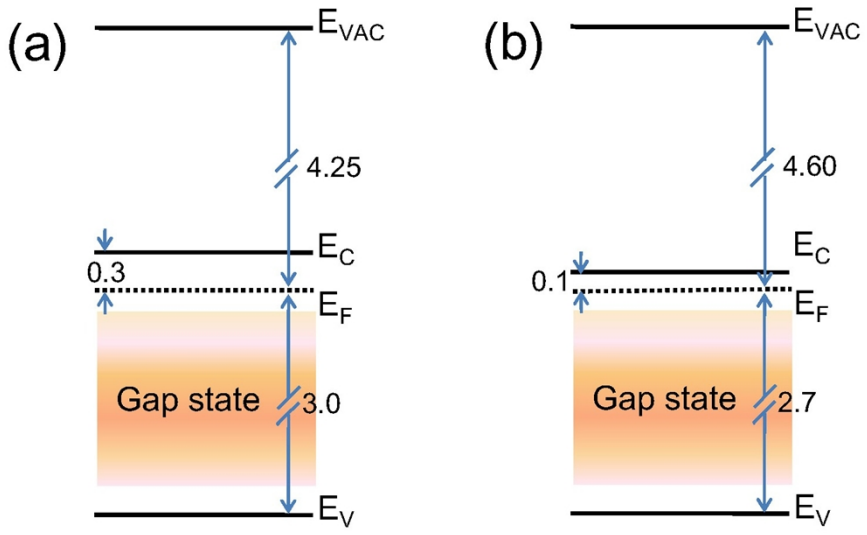

Figure S2 (a) the band structure of WO_3. (b) The band structure of V_2O_{5-x}. In these two materials, the vacuum level, conduction and valance band are the same on H-Si and CH_3-Si.